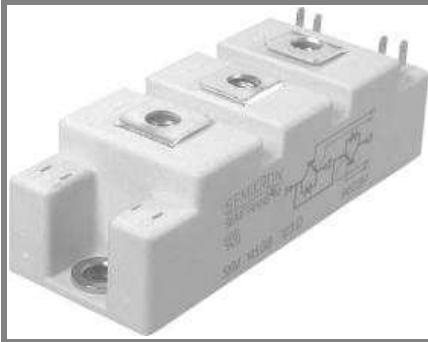




SEMITRANS® 2

Trench IGBT Modules

SKM195GB066D

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

Typical Applications*

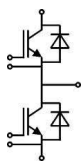
- AC inverter drives
- UPS
- Electronic welders

Remarks

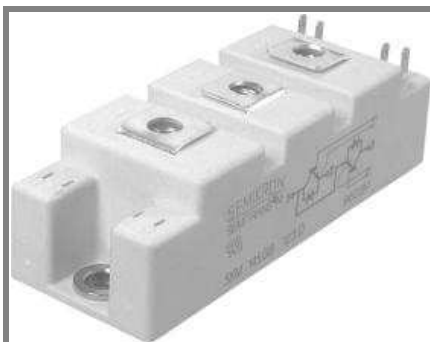
- Case temperature limited to $T_c = 125^\circ\text{C}$ max., product rel. results valid for $T_j \leq 150^\circ\text{C}$
- SC data: Use of soft R_G necessary!
- Take care of over-voltage caused by stray induct.

Absolute Maximum Ratings		T _{case} = 25°C, unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT				
V _{CES}	T _j = 25 °C	600	V	
I _C	T _j = 175 °C	T _c = 25 °C	265	A
		T _c = 80 °C	200	A
I _{CRM}	I _{CRM} =2xI _{Cnom}	400	A	
V _{GES}		± 20	V	
t _{psc}	V _{CC} = 360 V; V _{GE} ≤ 15 V; T _j = 150 °C V _{CES} < 600 V	6	μs	
Inverse Diode				
I _F	T _j = 175 °C	T _c = 25 °C	200	A
		T _c = 80 °C	130	A
I _{FRM}	I _{FRM} =2xI _{Fnom}	400	A	
I _{FSM}	t _p = 10 ms; sin.	T _j = 175 °C	1400	A
Module				
I _{t(RMS)}		200	A	
T _{vj}		- 40 ... + 175	°C	
T _{stg}		- 40 ... + 125	°C	
V _{isol}	AC, 1 min.	4000	V	

Characteristics			T _{case} = 25°C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 3,2 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C			0,13	0,38	mA
V _{CE0}	T _j = 25 °C			0,9	1	V
	T _j = 150 °C			0,85	0,9	V
r _{CE}	V _{GE} = 15 V T _j = 25°C			2,8	4,5	mΩ
	T _j = 150°C			4,3	6	mΩ
V _{CE(sat)}	I _{Cnom} = 200 A, V _{GE} = 15 V T _j = 25°C _{chiplev.}			1,45	1,9	V
	T _j = 150°C _{chiplev.}			1,7	2,1	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz			12,3		nF
C _{oes}				0,77		nF
C _{res}				0,37		nF
Q _G	V _{GE} = -8V...+15V			1500		nC
R _{Gint}	T _j = °C			2		Ω
t _{d(on)}	R _{Gon} = 3 Ω	V _{CC} = 300V I _C = 200A T _j = 150 °C V _{GE} = -8V/+15V		160		ns
t _r				68		ns
E _{on}	R _{Goff} = 3 Ω			14		mJ
t _{d(off)}			520		ns	
t _f			49		ns	
E _{off}				8		mJ
R _{th(j-c)}	per IGBT				0,22	K/W



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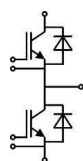
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- Take care of over-voltage caused by stray induct.

Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 200 \text{ A}; V_{GE} = 0 \text{ V}; T_j = 25^\circ\text{C}_{chiplev.}$		1,4	1,6	V
V_{F0}	$T_j = 25^\circ\text{C}$		0,95	1	V
r_F	$T_j = 25^\circ\text{C}$		2,3	3	mΩ
I_{RRM}	$I_F = 200 \text{ A}; T_j = 150^\circ\text{C}$		100		A
Q_{rr}	$di/dt = 2000 \text{ A}/\mu\text{s}$		30		μC
E_{rr}	$V_{GE} = -8 \text{ V}; V_{CC} = 300 \text{ V}$		5,6		mJ
$R_{th(j-c)D}$	per diode			0,4	K/W
Module					
L_{CE}				30	nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25^\circ\text{C}$	0,75		mΩ
		$T_{case} = 125^\circ\text{C}$	1		mΩ
$R_{th(c-s)}$	per module			0,05	K/W
M_s	to heat sink M6		3	5	Nm
M_t	to terminals M5		2,5	5	Nm
w				150	g

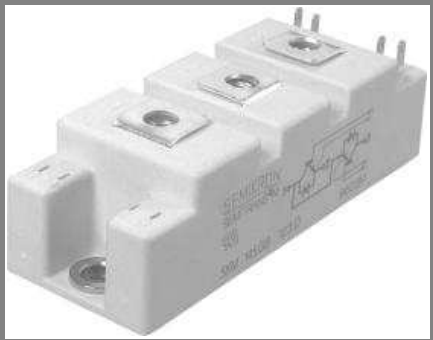
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.



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Z_{th}			
Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	$i = 1$	160	mk/W
R_i	$i = 2$	41	mk/W
R_i	$i = 3$	16	mk/W
R_i	$i = 4$	3	mk/W
τ_{u_i}	$i = 1$	0,0276	s
τ_{u_i}	$i = 2$	0,0406	s
τ_{u_i}	$i = 3$	0,001	s
τ_{u_i}	$i = 4$	0,0011	s
$Z_{th(j-c)D}$			
R_i	$i = 1$	250	mk/W
R_i	$i = 2$	110	mk/W
R_i	$i = 3$	35	mk/W
R_i	$i = 4$	5	mk/W
τ_{u_i}	$i = 1$	0,054	s
τ_{u_i}	$i = 2$	0,012	s
τ_{u_i}	$i = 3$	0,0015	s
τ_{u_i}	$i = 4$	0,0007	s



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